

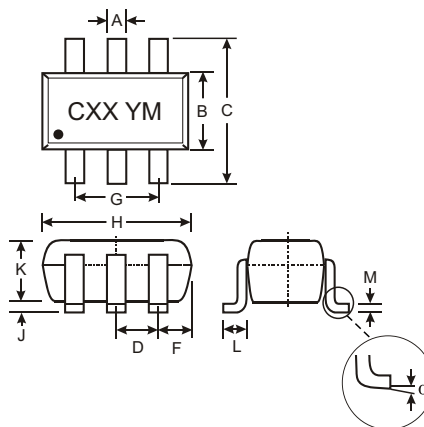
COMPLEMENTARY NPN/PNP PRE-BIASED SMALL SIGNAL SOT-363 DUAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Lead-Free Device

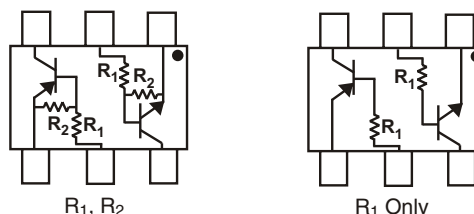
Mechanical Data

- Case: SOT-363, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: Date Code and Marking Code (See Diagrams & Page 3)
- Weight: 0.006 grams (approx.)
- Ordering Information (See Page 3)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

P/N	R1 (NOM)	R2 (NOM)	MARKING
DCX122LU	0.22K	10K	C81
DCX142JU	0.47K	10K	C82
DCX122TU	0.22K	OPEN	C83
DCX142TU	0.47K	OPEN	C84



SCHEMATIC DIAGRAM

Maximum Ratings NPN Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-5 to +6	V
Input Voltage	V _{EBO} (MAX)	5	V
Output Current	I _C	100	mA
Power Dissipation (Note 2, 3)	P _d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 2)	R _{θJA}	625	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Note: 1. If lead-bearing terminal plating is required, please contact your Diodes Inc. sales representative for availability and minimum order details.
 2. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. 150mW per element must not be exceeded.

Maximum Ratings PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	-50	V
Input Voltage	DCX122LU DCX142JU V_{IN}	+5 to -6 +5 to -6	V
Input Voltage	DCX122TU DCX142TU $V_{EBO (MAX)}$	-5	V
Output Current	All I_C	-100	mA
Power Dissipation (Note 2,3)	P_d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 2,3)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Note: 1. If lead-bearing terminal plating is required, please contact your Diodes Inc. sales representative for availability and minimum order details.
 2. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. 150mW per element must not be exceeded.

Electrical Characteristics NPN Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified **R1, R2 Types**

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DCX122LU DCX142JU $V_{I(off)}$	0.3 0.3	—	—	V	$V_{CC} = 5V, I_O = 100\mu A$
	DCX122LU DCX142JU $V_{I(on)}$	—	—	2.0 2.0	V	$V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 20mA$
Output Voltage	$V_{O(on)}$	—	—	0.3V	V	$I_O/I_I = 5mA/0.25mA$
Input Current	DCX122LU DCX142JU I_I	—	—	28 13	mA	$V_I = 5V$
Output Current	$I_{O(off)}$	—	—	0.5	μA	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	DCX122LU DCX142JU G_I	56 56	—	—	—	$V_O = 5V, I_O = 10mA$
Gain-Bandwidth Product*	f_T	—	200	—	MHz	$V_{CE} = 10V, I_E = 5mA,$ $f = 100MHz$

* Transistor - For Reference Only

Electrical Characteristics NPN Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified **R1 Only**

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	$I_C = 50\mu A$
Collector-Emitter Breakdown Voltage	BV_{CEO}	40	—	—	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	DCX122TU DCX142TU BV_{EBO}	5	—	—	V	$I_E = 50\mu A$ $I_E = 50\mu A$
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 50V$
Emitter Cutoff Current	DCX122TU DCX142TU I_{EBO}	—	—	0.5 0.5	μA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 5mA, I_B = 0.25mA$
DC Current Transfer Ratio	DCX122TU DCX142TU h_{FE}	100 100	250 250	600 600	—	$I_C = 1mA, V_{CE} = 5V$
Gain-Bandwidth Product*	f_T	—	200	—	MHz	$V_{CE} = 10V, I_E = -5mA,$ $f = 100MHz$

* Transistor - For Reference Only

Electrical Characteristics PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified R1, R2 Types

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DCX122LU DCX142JU	$V_{I(off)}$	-0.3 -0.3	—	—	V	$V_{CC} = -5V, I_O = -100\mu A$
	DCX122LU DCX142JU	$V_{I(on)}$	—	—	-2.0 -2.0	V	$V_O = -0.3V, I_O = -20mA$ $V_O = -0.3V, I_O = -20mA$
Output Voltage		$V_{O(on)}$	—	—	-0.3V	V	$I_O/I_I = -5mA/-0.25mA$
Input Current	DCX122LU DCX142JU	I_I	—	—	-28 -13	mA	$V_I = -5V$
Output Current		$I_{O(off)}$	—	—	-0.5	μA	$V_{CC} = -50V, V_I = 0V$
DC Current Gain	DCX122LU DCX142JU	G_I	56 56	—	—	—	$V_O = -5V, I_O = -10mA$
Gain-Bandwidth Product*		f_T	—	200	—	MHz	$V_{CE} = -10V, I_E = -5mA,$ $f = 100MHz$

* Transistor - For Reference Only

Electrical Characteristics PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified R1-Only Types

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV_{CBO}	-50	—	—	V	$I_C = -50\mu A$
Collector-Emitter Breakdown Voltage		BV_{CEO}	-40	—	—	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	DCX122TU DCX142TU	BV_{EBO}	-5	—	—	V	$I_E = -50\mu A$ $I_E = -50\mu A$
Collector Cutoff Current		I_{CBO}	—	—	-0.5	μA	$V_{CB} = -50V$
Emitter Cutoff Current	DCX122TU DCX142TU	I_{EBO}	—	—	-0.5 -0.5	μA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	—	—	-0.3	V	$I_C = -5mA, I_B = -0.25mA$
DC Current Transfer Ratio	DCX122TU DCX142TU	h_{FE}	100 100	250 250	600 600	—	$I_C = -1mA, V_{CE} = -5V$
Gain-Bandwidth Product*		f_T	—	200	—	MHz	$V_{CE} = -10V, I_E = 5mA,$ $f = 100MHz$

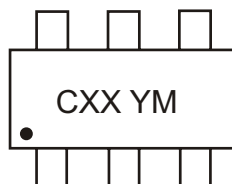
* Transistor - For Reference Only

Ordering Information (Note 4)

Device	Packaging	Shipping
DCX122LU-7	SOT-363	3000/Tape & Reel
DCX142JU-7	SOT-363	3000/Tape & Reel
DCX122TU-7	SOT-363	3000/Tape & Reel
DCX142TU-7	SOT-363	3000/Tape & Reel

Notes: 1. If lead-bearing terminal plating is required, please contact your Diodes Inc. sales representative for availability and minimum order details.

 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information


CXX = Product Type Marking Code
 See Sheet 1 Diagrams
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

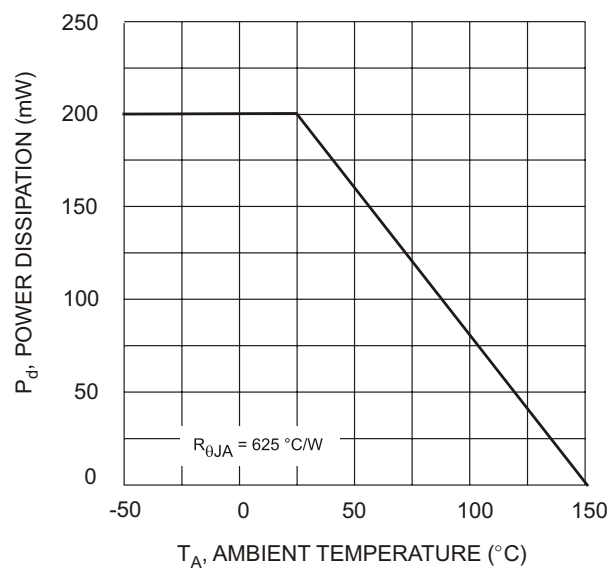


Fig. 1 Power Derating Curve

(150mW per element must not be exceeded).